

# Silicon Diode

## **1N5615GP**

Fast Switching Rectifier

200V / 1A

# DATASHEET

OEM – General Semiconductor

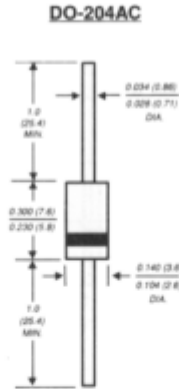
Source: General Semiconductor Databook 1998

# 1N5615GP THRU 1N5623GP

## GLASS PASSIVATED JUNCTION FAST SWITCHING RECTIFIER

Reverse Voltage - 200 to 1000 Volts Forward Current - 1.0 Ampere

**PATENTED\***



Dimensions in inches and (millimeters)

\* Glass-plastic encapsulation technique is covered by Patent No. 3,996,602 and brazed-lead assembly by Patent No. 3,930,306



### FEATURES

- ◆ Plastic package has Underwriters Laboratory Flammability Classification 94V-0
- ◆ High temperature metallurgically bonded construction
- ◆ Glass passivated cavity-free junction
- ◆ Capable of meeting environmental standards of MIL-S-19500
- ◆ Fast switching for high efficiency
- ◆ 1.0 Ampere operation at  $T_A=55^\circ\text{C}$  with no thermal runaway
- ◆ High temperature soldering guaranteed:  $350^\circ\text{C}/10\text{seconds}$ , 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

### MECHANICAL DATA

**Case:** JEDEC DO-204AC molded plastic over glass body  
**Terminals:** Plated axial leads, solderable per MIL-STD-750, Method 2026  
**Polarity:** Color band denotes cathode end  
**Mounting Position:** Any  
**Weight:** 0.015 ounce, 0.4 gram

### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at  $25^\circ\text{C}$  ambient temperature unless otherwise specified.

	SYMBOLS	1N 5615GP	1N 5617GP	1N 5619GP	1N 5621GP	1N 5623GP	UNITS
* Maximum repetitive peak reverse voltage	VRRM	200	400	600	800	1000	Volts
* Maximum RMS voltage	VRMS	140	280	420	560	700	Volts
* Maximum DC blocking voltage	VDC	200	400	600	800	1000	Amps
* Maximum average forward rectified current 0.375" (9.5mm) lead length at $T_A=55^\circ\text{C}$	$I_{(AV)}$	1.0					Amp
* Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	50.0					Amps
Maximum instantaneous forward voltage at 1.0A	$V_F$	1.2					Volts
Maximum DC reverse current at rated DC blocking voltage	$I_R$	0.5 25.0					$\mu\text{A}$
$T_A=25^\circ\text{C}$ $T_A=100^\circ\text{C}$							
*Maximum reverse recovery time (NOTE 1)	$t_{rr}$	150	250	300	500		ns
Typical junction capacitance (NOTE 2)	$C_J$	25.0					pF
Typical thermal resistance (NOTE 3)	$R_{\theta JA}$	45.0					$^\circ\text{C}/\text{W}$
* Operating junction and storage temperature range	$T_J, T_{STG}$	-65 to +175					$^\circ\text{C}$

**NOTES:**

- (1) Reverse recovery test conditions:  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{rr}=0.25\text{A}$
  - (2) Measured at 1.0 MHz and applied reverse voltage of 4.0 Volts
  - (3) Thermal resistance from junction to ambient at 0.375" (9.5mm) lead length, P.C.B. mounted
- \* JEDEC registered values

**RATINGS AND CHARACTERISTIC CURVES 1N5615GP THRU 1N5623GP**

